	part name	description	Vdss	Pdiss Watts 25*C	derate watts above 25*C	Id(A)	Transconductance	Reverse transfer C Crss (pf)	Output C Crss (pf)	Input C Crss (pf)	Test Conditions		
1	**C3M0016120D**	Silicon Carbide Power MOSFET	1200	556		115	53S, VDS= 20 V, IDS= 75 A	13	230	6085	VGS = 0 V, VDS = 1000 V f = 100 KHz VAC = 25 mV		
2	**C3M0120090D**	Silicon Carbide Power MOSFET	900	97		23	7.7S, VDS= 20 V, IDS= 15 A	3	40	350			
3	**FCA22N60N**		600	205	1.64	22	22S,	3	75.9	1950			
4	**FCA47N60**		600	417	3.33	47	40S	250	3200	5900			
5	**FDA24N50F**		500	270	2.2	20	30S	32	450	3240			
6	**FDA59N30**		300	500	4	59	52S, VDS = 40 V, ID = 29.5 A	80	710	3590			
7	**FDL100N50F**		500	2500	20	100	95S, VDS = 20V, ID = 50A	64	1700	12000			
8	**FDP083N15A-D**		150	294	1.96	117	139S, VDS = 10V, ID = 75A	100	1445	4645			
9	**FQA28N15**	N-Channel QFET MOSFET	150	227	1.52	33	20S, VDS = 40 V, ID = 16.5 A	50	260	1250			
10	**FQA40N25**	N-Channel QFET® MOSFET	250	280	2.2	40		70	620	3100	VGS = 0V, VDS = 20V, f = 1MHz		
11	**FQA40N25**		250	280	2.22	40	29S, VDS = 50V, ID =25A	70	620	3100			
12	**FQH44N10**		100	180	1.2	48	31S, VDS = 40 V, ID = 24 A	85	125	1400			
13	**IRFP150**		100	160	1.1	42	14S, VDS = 20 V, ID = 22 Ab	230	450	1900			
14	**IRFP240**	Power MOSFET	200	150		20	6.9S, VDS = 50 V, ID = 12 Ab	130	400	1300	VGS = 0V, VDS = 25V, f = 1MHz		
15	**IRFP340**		400	150	1.25	11	7.7S, VDS= 50 V, IDS= 15 A	130	400	1400			
16	**IRFP450**		500	190		14	9.3S	340	720	1600			
17	**IRFP460**		500	280		20	13S, VDS = 50 V, ID = 12 Ab	350	870	4200			
18	**IRFP4668PbF**		200	520	3.5	130	150S, VDS = 50V, ID = 81A	160	810	10720			
19	**IRFP90N20D**		200	580		94	39S	170	1070	6040			
20	**IXFH26N50**		500	300		26	21S	135	450	4200			
21	**IXFH69N30P**	HiPerFETTM Power MOSFET	300	500		69		190	760	4960	VGS = 0V, VDS = 25V, f = 1MHz		
22	**IXFN140N20P**		200	680		115	50S, VDS= 10 V; ID = 70 A	280	630	7500			
23	**IXTH16N50D2**	Depletion Mode	500	695		16	12S, VDS = 30V, ID = 8A	130	515	5250			
24	**IXTH64N10L2**		100	357		64	21S, VDS = 10V, ID = 0.5 • ID25, Note 1	235	720	3620			
25	**IXTH6N50D2**	Depletion Mode	500	300		6	4.5S	64	255	2800			
26	**IXTK82N25P**		250	500		82	52S, VDS = 10 V, ID = 29.5 A	210	900	4800			
27	**IXTQ82N25P**		250	500		82	52S, VDS = 10 V, ID = 29.5 A	210	900	4800			
28	**IXTT82N25P**		250	500		82	52S, VDS = 10 V, ID = 29.5 A	210	900	4800			
29	**UJ3N065080K3S**	650V SiC Normally-On JFET	650	175		32		88	94	630	VDS = 100V, VGS = -20V, f = 100kHz		www.unitedsic.com
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